

MOSFET – Power, Single N-Channel

100 V, 14 mΩ, 46 A

NVMFS016N10MCL

Features

- Small Footprint (5x6 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- AEC-Q101 Qualified and PPAP Capable
- NVMFWS016N10MCL – Wettable Flank Products
- These Devices are Pb-Free, Halogen Free/BFR Free, Beryllium Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	100	V
Gate-to-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current $R_{\theta JC}$ (Note 1)	Steady State	$T_C = 25^\circ\text{C}$	I_D 46 A
		$T_C = 100^\circ\text{C}$	32
Power Dissipation $R_{\theta JC}$ (Note 1)	Steady State	$T_C = 25^\circ\text{C}$	P_D 64 W
		$T_C = 100^\circ\text{C}$	32
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2)	Steady State	$T_A = 25^\circ\text{C}$	I_D 10.9 A
		$T_A = 100^\circ\text{C}$	7.7
Power Dissipation $R_{\theta JA}$ (Notes 1, 2)	Steady State	$T_A = 25^\circ\text{C}$	P_D 3.6 W
		$T_A = 100^\circ\text{C}$	1.8
Pulsed Drain Current	$T_A = 25^\circ\text{C}, t_p = 10 \mu\text{s}$	I_{DM} 243	A
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +175	$^\circ\text{C}$
Source Current (Body Diode)	I_S	49	A
Single Pulse Drain-to-Source Avalanche Energy ($I_{L(pk)} = 2.2 \text{ A}$)	E_{AS}	358	mJ
Lead Temperature Soldering Reflow for Soldering Purposes (1/8" from case for 10 s)	T_L	260	$^\circ\text{C}$

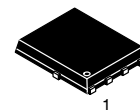
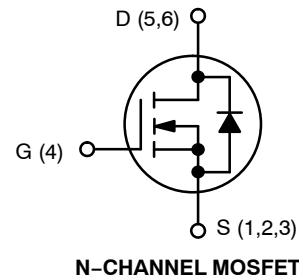
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

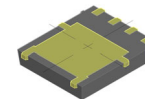
Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State (Note 1)	$R_{\theta JC}$	2.35	$^\circ\text{C}/\text{W}$
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	41	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using 1 in² pad size, 1 oz. Cu pad.

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
100 V	14 mΩ @ 10 V	46 A
	20 mΩ @ 4.5 V	

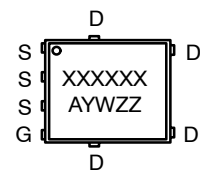
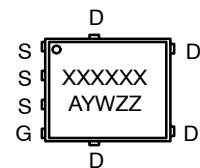


DFN5
CASE 488AA
STYLE 1



DFNW5
(for WF Version)
CASE 507BA

MARKING DIAGRAM



XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 5 of this data sheet.

NVMFS016N10MCL

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	100			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 250\ \mu\text{A}, \text{ref to } 25^\circ\text{C}$		60		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 100\text{ V}$	$T_J = 25^\circ\text{C}$		1	μA
			$T_J = 125^\circ\text{C}$		100	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = 20\text{ V}$			100	nA

ON CHARACTERISTICS

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 64\ \mu\text{A}$	1		3	V
Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$	$I_D = 250\ \mu\text{A}, \text{ref to } 25^\circ\text{C}$		-5.6		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 11\text{ A}$		11.5	14	$\text{m}\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 9\text{ A}$		16	20	
Forward Transconductance	g_{FS}	$V_{DS} = 10\text{ V}, I_D = 11\text{ A}$		42		S
Gate-Resistance	R_G	$T_A = 25^\circ\text{C}$		1.2		Ω

CHARGES & CAPACITANCES

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 50\text{ V}$		1250		pF
Output Capacitance	C_{OSS}			460		
Reverse Transfer Capacitance	C_{RSS}			8		
Total Gate Charge	$Q_G(\text{TOT})$	$V_{GS} = 4.5\text{ V}, V_{DS} = 50\text{ V}, I_D = 9\text{ A}$		9.0		nC
Total Gate Charge	$Q_G(\text{TOT})$	$V_{GS} = 10\text{ V}, V_{DS} = 50\text{ V}, I_D = 11\text{ A}$		19		
Threshold Gate Charge	$Q_G(\text{TH})$			2.1		
Gate-to-Source Charge	Q_{GS}			3.7		
Gate-to-Drain Charge	Q_{GD}			2.0		
Plateau Voltage	V_{GP}			2.8		

SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 10\text{ V}, V_{DS} = 50\text{ V}, I_D = 11\text{ A}, R_G = 6\ \Omega$		10		ns
Rise Time	t_r			3.4		
Turn-Off Delay Time	$t_{d(OFF)}$			26		
Fall Time	t_f			4.2		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 11\text{ A}$	$T_J = 25^\circ\text{C}$		0.84	1.3	V
			$T_J = 125^\circ\text{C}$		0.72		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, di_S/dt = 100\text{ A}/\mu\text{s}, I_S = 6\text{ A}$		34		ns	
Reverse Recovery Charge	Q_{RR}			24		nC	
Charge Time	t_a			16		ns	
Discharge Time	t_b			17		ns	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Switching characteristics are independent of operating junction temperatures

TYPICAL CHARACTERISTICS

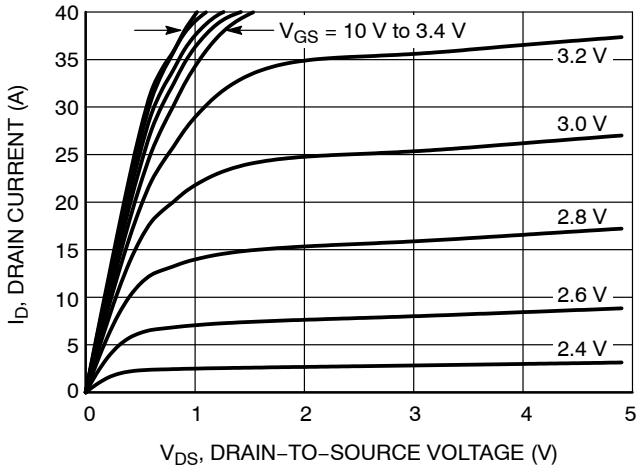


Figure 1. On-Region Characteristics

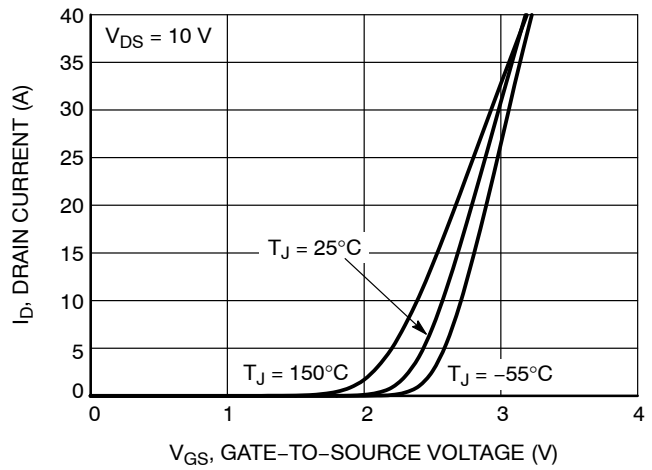


Figure 2. Transfer Characteristics

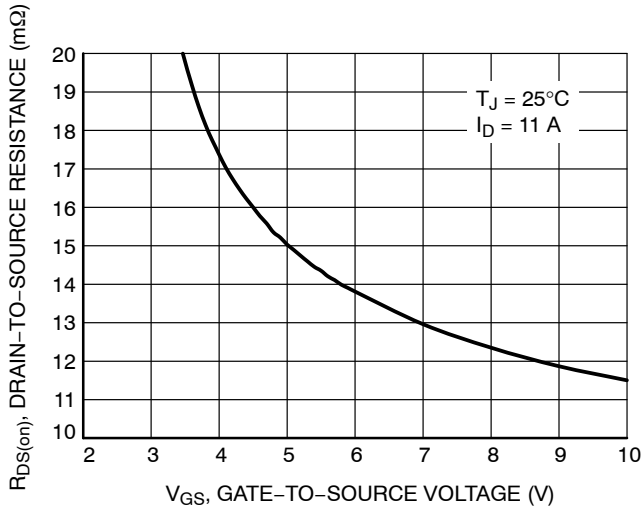


Figure 3. On-Resistance vs. Gate-to-Source Voltage

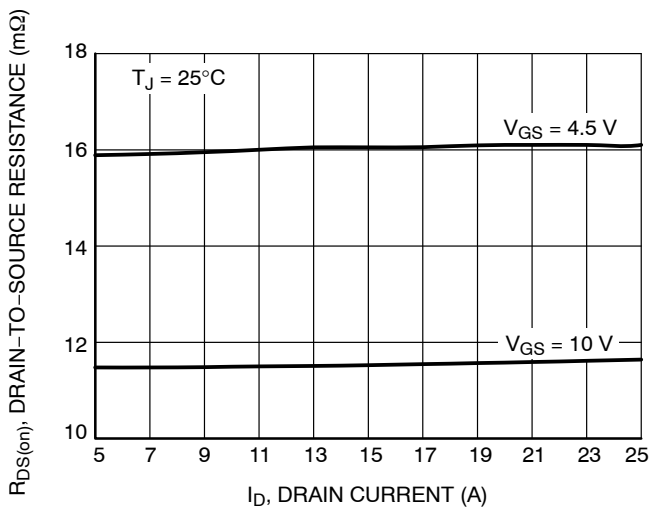


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

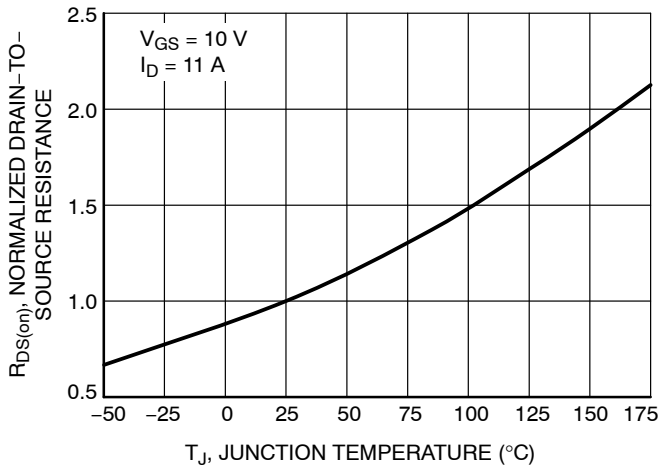


Figure 5. On-Resistance Variation with Temperature

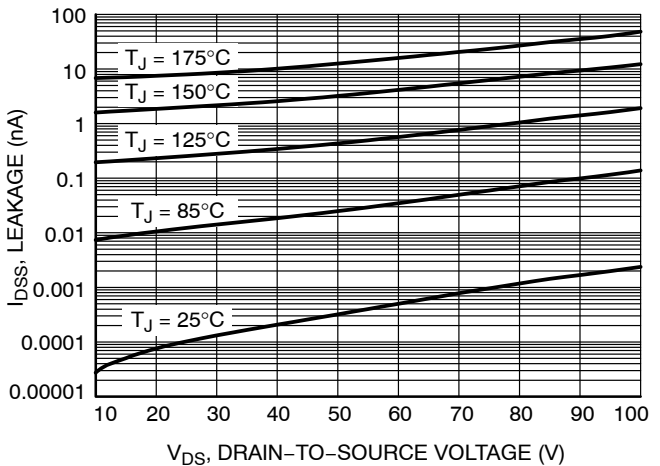


Figure 6. Drain-to-Source Leakage Current vs. Voltage

NVMFS016N10MCL

TYPICAL CHARACTERISTICS

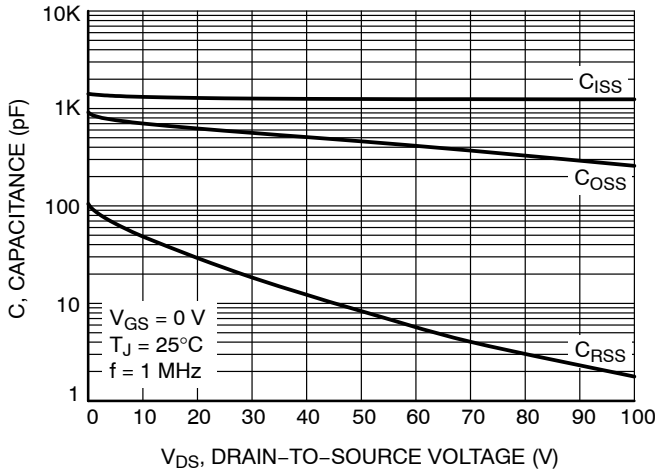


Figure 7. Capacitance Variation

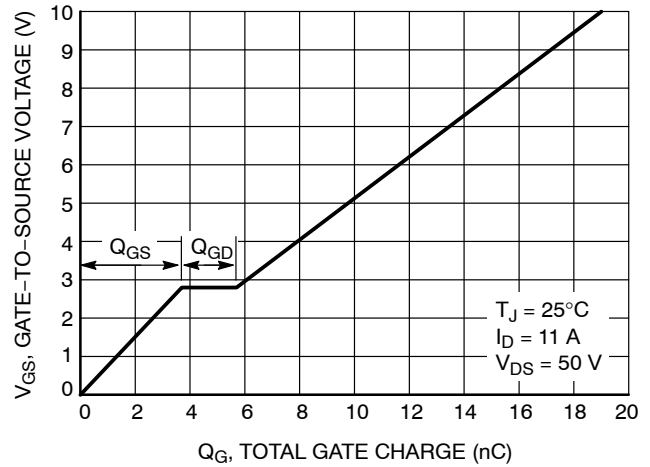


Figure 8. Gate-to-Source Voltage vs. Total Charge

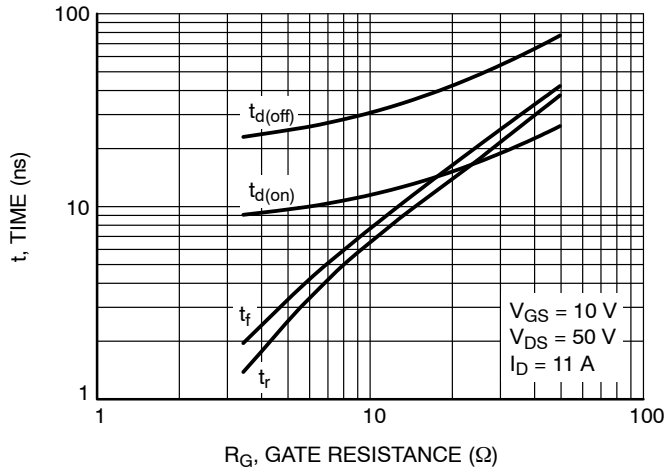


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

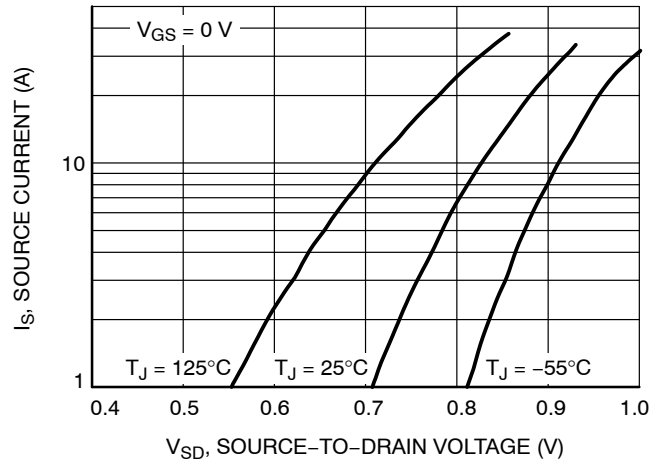


Figure 10. Diode Forward Voltage vs. Current

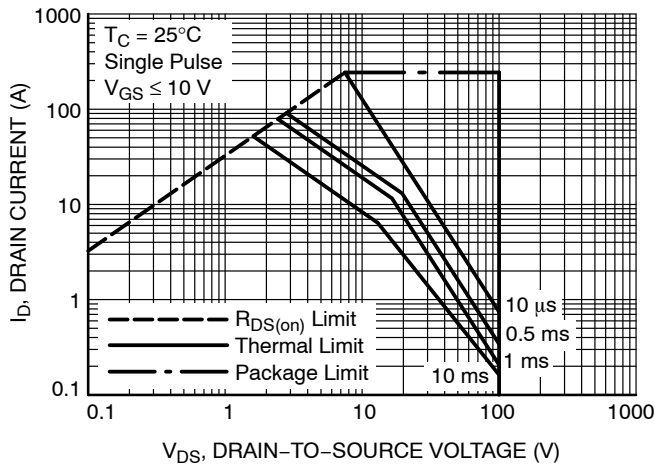


Figure 11. Maximum Rated Forward Biased Safe Operating Area

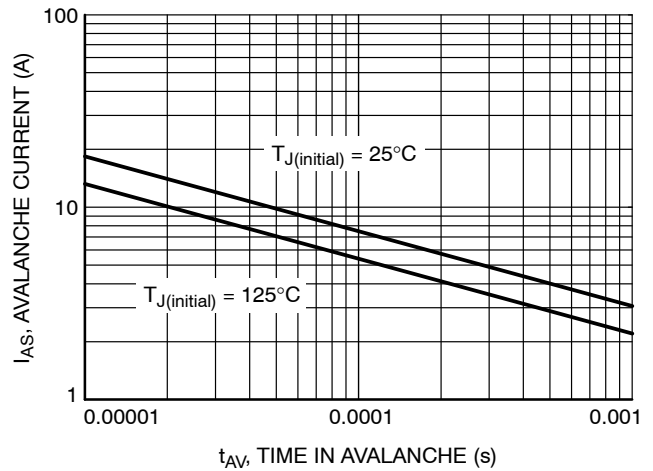


Figure 12. Maximum Drain Current vs. Time in Avalanche

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TYPICAL CHARACTERISTICS

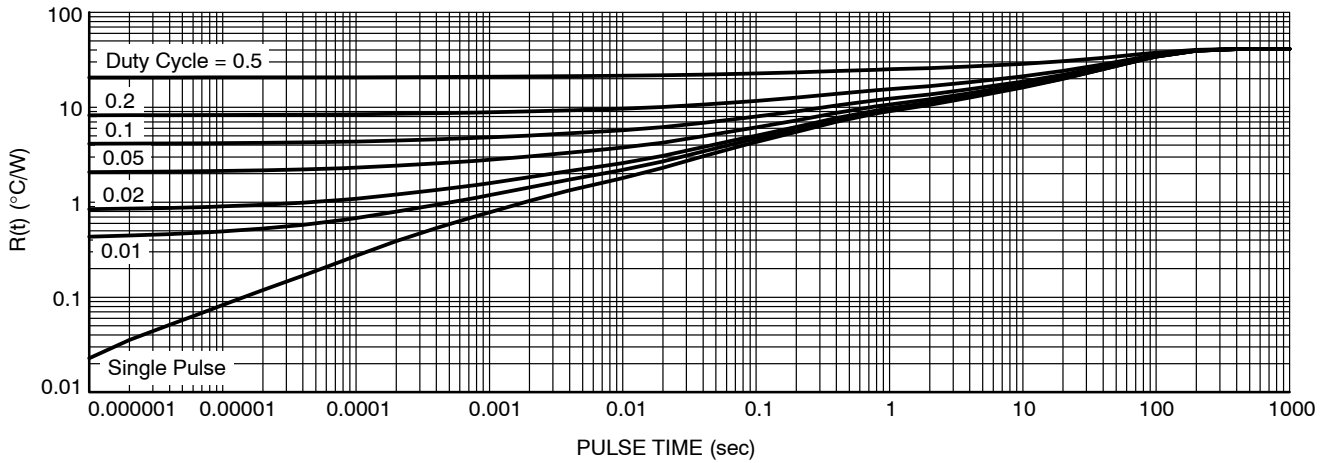


Figure 13. Transient Thermal Impedance

DEVICE ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
NVMFS016N10MCLT1G	016L10	DFN5 (Pb-Free)	1500 / Tape & Reel
NVMFWS016N10MCLT1G	016W10	DFN5 (Wettable Flank, Pb-Free)	1500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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PACKAGE DIMENSIONS

DFN5 5x6, 1.27P
(SO-8FL)
CASE 488AA
ISSUE N

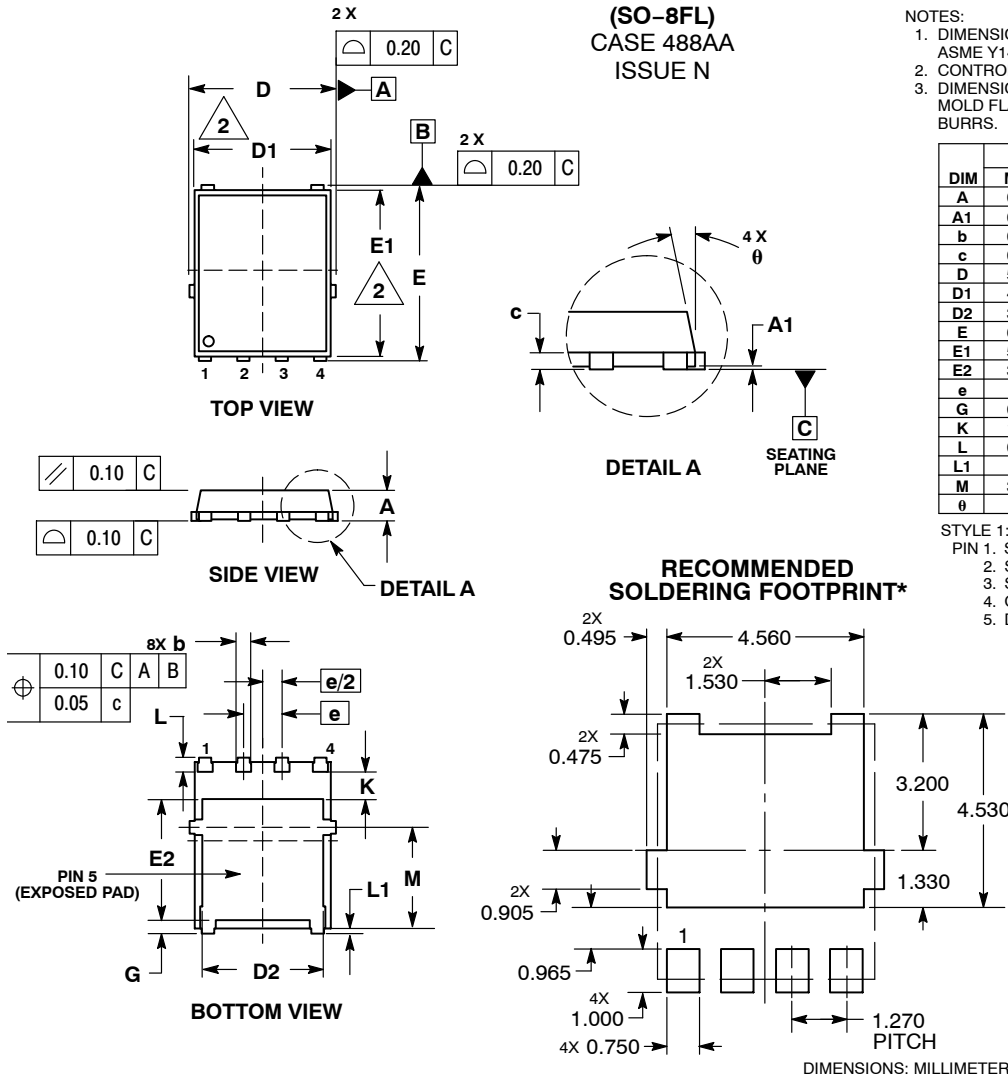
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.125 REF		
M	3.00	3.40	3.80
θ	0°	---	12°

STYLE 1:

1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN

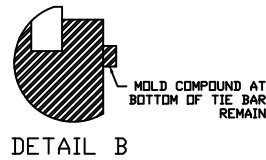
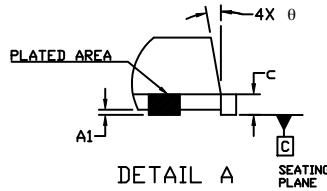
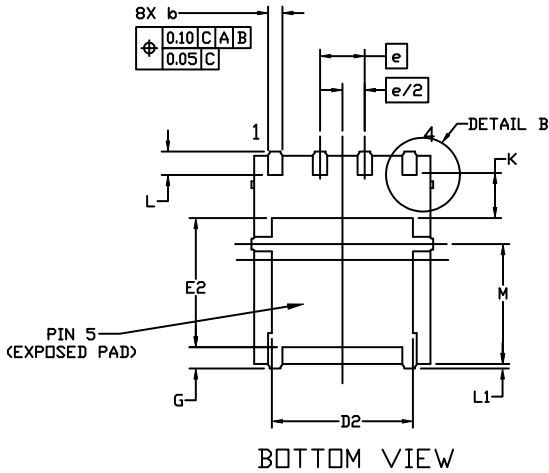
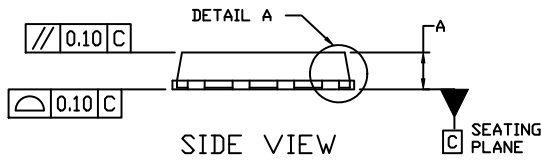
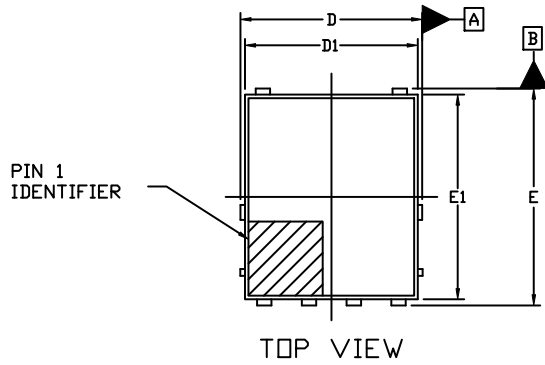


*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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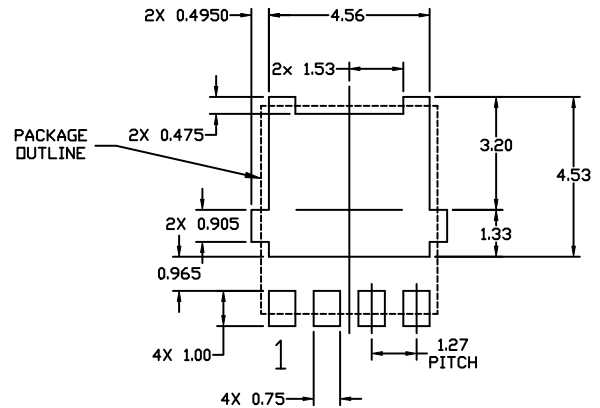
PACKAGE DIMENSIONS

DFNW5 5x6 (FULL-CUT SO8FL WF) CASE 507BA ISSUE A



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
 2. CONTROLLING DIMENSION: MILLIMETERS
 3. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
 4. THIS PACKAGE CONTAINS WETTABLE FLANK DESIGN FEATURES TO AID IN FILLET FORMATION ON THE LEADS DURING MOUNTING.

MILLIMETERS			
DIM	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.150 REF		
M	3.00	3.40	3.80
θ	0°	---	12°



RECOMMENDED MOUNTING FOOTPRINT

- * For additional information on our Pb-Free strategy and soldering details, please download the ION Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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